Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S18	13508	single same drain same electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR.	ON	2007/02/20 12:47
S19	59	single near drain near electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 13:10
S20	181996	transistor same drain same source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/20 13:11
S21	124378	tft or (thin near film near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2007/02/20 13:11
S22	27677	S21 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 13:11
S23	16533	chalcogen\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 13:11
S24	655185	tellerium or selenium or selenide or sulfur or sulfide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 13:11
S25	798	S21 same (S23 or S24)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 13:17
S26	275233	nonvolatile or non-volatile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 13:12

S27	20	S25 and S26	US-PGPUB;	OR	ON	2007/02/20 13:17
32,	20		USPAT; USOCR; EPO; JPO; DERWENT			2007/02/20 13.17
S28	15	S27 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 13:18
S29	4	"7123535"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR -	ON	2007/02/20 15:37
S30	3	"7110284"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:37
S31	2	"7098478"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/20 15:38
S32	3	"7078273"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:38
S33	2	"7071485"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/20 15:40
S34	6	"6946704"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:41
S35	4	"6903966"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:41

S36	5	"7038961"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:42
S37	4	"7002831"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:42
S38	6	"6946704 <u>"</u>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:43
S39	2	"7071485"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:44
S40	2	"7116093"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:44
S41	7	"6771535"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/20 15:44

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S10 6	2289788	display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S10 7	377562	pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S10 8	92968	tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S10 9	85983	phase-change or (phase near change)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 0	1993458	memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 1	275628	nonvolatile or non-volatile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 2	5920	S109 same S110	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 3	1123	S112 same S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 4	29	S113 and S107 and S106	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S11 5	3	S114 and S108	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 6	58	"4432610"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 7	45	chalconide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 8	16551	chalcogen\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S11 9	38378	S106 and S107 and S108	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR ·	ON	2007/02/22 16:24
S12 0	91	S118 and S119	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S12 1	2680574	storage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S12 2	5920	S109 same S110	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S12 3	1013	S122 same S118	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S12 4	25	S123 and S108	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S12 5	1	S124 and S107	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S12 6	2289788	display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2007/02/22 16:24
S12 7	377562	pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S12 8	92968	tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S12 9	85983	phase-change or (phase near change)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 0	1993458	memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 1	275628	nonvolatile or non-volatile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 2	5920	S129 same S130	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S13 3	1123	S132 same S131	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 4	29	S133 and S127 and S126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ÖR	ON	2007/02/22 16:24
S13 5	45	chalconide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 6	16551	chalcogen\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 7	38378	S126 and S127 and S128	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 8	2680574	storage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S13 9	5920	S129 same S130	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 0	1013	S139 same S136	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 1	25	S140 and S128	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2007/02/22 16:24

S14 2	1	S141 and S127	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 3	3	S134 and S128	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 4	. 58	"4432610"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 5	29	S133 and S127 and S126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 6	91	S136 and S137	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 7	25	S140 and S128	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2007/02/22 16:24
S14 8	10	S128 same S136	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S14 9	5016	S130 same S128	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 0	3815	S149 and S126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S15 1	2	S150 and S145	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 2	2660	S150 and S127	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 3	. 5	S152 and S136	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 4	72990	variable near resistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 5	15913	varistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 6	88049	S154 or S155	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 7	81513	thin near film near transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2007/02/22 16:24
S15 8	124504	S128 or S157	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S15 9	295	S156 same S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

64.5	22442	6496	T	Τ		
S16 0	224404	S126 and S127	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S16 1	209	S159 and S160	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/22 16:24
S16 2	39	S161 and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S16 3	2680574	storage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S16 4	,69	S161 and S163	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S16 5	2414	S158 and (S129 or S131 or S136) and S126 and S127	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S16 6	5	S159 and S136	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S16 7	44036	variable near resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02 <u>/</u> 22 16:24
S16 8	48	S167 same S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2007/02/22 16:24

S16 9	2325	S158 and (S129 or S131) and S126 and S127	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S17 0	18	S169 and S136	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S17 1	21133	S126 and S127 and (S129 or S131)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S17 2	103	S127 same (S129 or S131) same S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/22 16:24
S17 3	119803	S167 or S156	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/22 16:24
S17 4	3	S172 and S173	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S17 5	513	S173 same S131 same S130	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S17 6	1	S175 same S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S17 7	16	S175 and S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S17 8	161	S173 and S131 and S130 and S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S17 9	327	S173 same S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR ·	ON	2007/02/22 16:24
S18 0	4	S178 and S179	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S18 1	85983	phase-change or (phase near change)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S18 2	275628	nonvolatile or non-volatile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S18 3	1217	S181 same S182	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/22 16:24
S18 4	190	S181 near S182	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S18 5	5	"6621130"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S18 6	0	S185 and phase	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S18 7	0	S185 and phase-change	US-PGPUB; USPAT;	OR	ON	2007/02/22 16:24
			USOCR; EPO; JPO; DERWENT			
S18 8	0	S185 and ge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S18 9	. 0	S185 and te	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S19 0	0	S185 and chalcogen\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S19 1	350	semiconductor same S183	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S19 2	59	semiconductor same S184	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR -	ON	2007/02/22 16:24
S19 3	1	"5166758".PN.	USPAT; USOCR	OR	ON	2007/02/22 16:24
S19 4	10275	organic near light near emitting near diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S19 5	2289788	display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S19 6	. 741	S194 same apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S19 7	471	S196 same display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S19 8	2	"6621130" and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR .	ON	2007/02/22 16:24
S19 9	. 8	"5335219" and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 0	71	"5335219" and litho\$7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 1	124504	tft or (thin near film near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 2	104985	variable near (resistance or resistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 3	10824	S201 same resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 4	173	S202 and S203	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 5	96	S202 same S201	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24

S20 6	3402	S202 same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 7	4	"6621130" and cell .	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S20 8	108	S204 not S205	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
\$20 9	9	S208 and S206	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/02/22 16:24
S21 0	4	"6621130" and cells	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON .	2007/02/22 16:24